

TOSHIBA

TPS823

TOSHIBA PHOTO IC SILICON EPITAXIAL PLANAR

TPS823

PHOTO IC FOR PLASTIC FIBER / POLYMER CLAD FIBER

Unit in mm

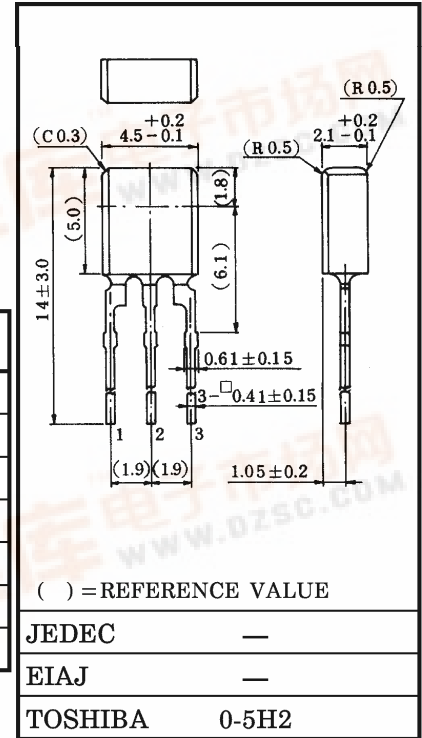
TPS823 contains a light receiving IC integrating photo diode, amplifier circuit, open collector output circuit, in 1 chip.

Output is directly connectable to IC as it changes digitally.

When light is received, output becomes low level.

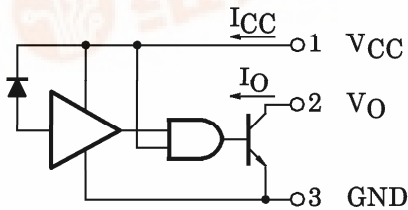
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	5.5	V
Output Voltage	V _O	5.5	V
Output Current	I _O	50	mA
Output Collector Power Dissipation	P _O	85	mW
Operating Temperature Range	T _{opr}	-25~85	°C
Storage Temperature Range	T _{stg}	-40~100	°C
Lead Temperature : Time	T _{sol}	260°C·3s	



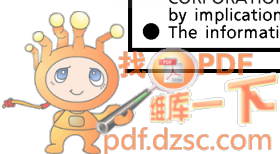
Weight : 0.12g (TYP.)

PIN CONNECTION



961001EAA2

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

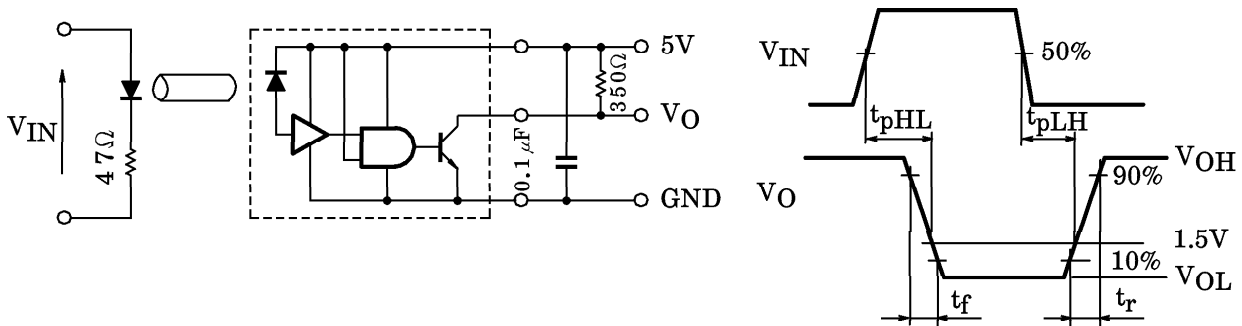


OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Supply Voltage		V _{CC}	Ta=25°C	4.5	5.0	5.5	V
Output Current	Low Level	V _{OL}	I _{OL} =13mA, V _{CC} =5.5V, P _f =120μW	—	0.4	0.6	V
	High Level	I _{OH}	V _{CC} =V _O =5.5V	—	0.001	250	μA
Supply Current	Low Level	I _{CCCL}	V _{CC} =5.5V, P _f =120μW	—	12	18	mA
	High Level	I _{CCCH}	V _{CC} =5.5V	—	7	15	
“L”→“H” Threshold Radiant Incidence (Note)		P _{fHL}	V _{CC} =5.5V, Ta=25°C, λ _p =660nm, V _O =1.5V	—	26	60	μW
				—	-15.9	-12.3	dBm
Switching Time	Propagation Delay Time	“L”→“H”	t _{pLH}	Ta=25°C, V _{CC} =5V, R _L =350Ω, P _f =0↔120μW	—	70	ns
		“H”→“L”	t _{pHL}		—	80	
		Rise Time	t _r		—	20	
		Fall Time	t _f		—	45	

Note : Equivalent to the optical output at the end of a plastic fiber in the core diameter 980μm.

SWITCHING TIME TEST CIRCUIT



PRECAUTION

Please be careful of the followings.

- Soldering temperature : 260°C MAX. Soldering time : 3s MAX. (Soldering portion of lead : above 2mm from the body of the device).
- As the output photo IC contains a very high sensitivity amplifier, a bypass capacitor 0.1μF having good high frequency characteristic shall be mounted between Pins 1 and 3 at a position within 1cm from the pins for preventing oscillation. It not, proper speed or ON/OFF operation may not be obtained.
- Pin surge voltage (Note) : MAX 150V (Note) Surge voltage chargeable between optional 2 pins at storage charge below 200pF.
- Tensile strength of lead : MAX 100g

